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November 2013

FDD850N10L

N-Channel PowerTrench[®] MOSFET 100 V, 15.7 A, 75 m Ω

Features

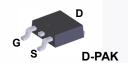
- $R_{DS(on)}$ = 61 m Ω (yp.) @ V_{GS} = 10 V, I_D = 12 A
- $R_{DS(on)}$ = 64 $m\Omega$ (Typ.) @ V_{GS} = 5 V, I_D = 12 A
- Low Gate Charge (Typ. 22.2 nC)
- Low C_{rss} (Typ. 42 pF)
- · Fast Switching
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

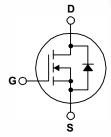
Description

This N-Channel MOSFET is produced using Fairchld Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance and maintain superior switching performance.

Application

- · Consumer Appliances
- · LED TV and Monitor
- · Synchronous Rectification
- Uninterruptible Power Supply
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDD850N10L	Unit
V _{DSS}	Drain to Source Voltage			100	V
V _{GSS}	Gate to Source Voltage			±20	V
	Drain Current	- Continuous (T _C = 25°C)		15.7	^
'D	Drain Current	- Continuous (T _C = 100°C)		11.1	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	63	Α
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	41	mJ
dv/dt	Peak Diode Recovery dv/	dt	(Note 3)	6.0	V/ns
n	Dower Discinction	$(T_C = 25^{\circ}C)$		50	W
P_{D}	Power Dissipation	- Derate Above 25°C		0.33	W/°C
T _J , T _{STG}	Operating and Storage Te	emperature Range		-55 to +175	°C
T _L	Maximum Lead Temperat	ure for Soldering, 1/8" from Case for 5 S	Seconds	300	°C

Thermal Characteristics

Symbol	Parameter FDD850		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 87		*C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD850N10L	FDD850N10L	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}$	100	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.1	-	V/°C
ı	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	
I _{DSS} Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μA	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	-	2.5	V
D	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 12 A	-	61	75	mΩ
NDS(on)	R _{DS(on)} Static Drain to Source On Resistance	V _{GS} = 5 V, I _D = 12 A	-	64	96	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 15.7 A	-	31	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		1100	1465	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS}$			80	105	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12			42	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{GS} = 10 V		-	22.2	28.9	nC
Q _{g(tot)}	Total Gate Charge at 5V	V _{GS} = 5 V	V _{DS} = 80 V,	-	12.3	16.0	nC
Q_{gs}	Gate to Source Gate Charge		I _D = 15.7 A	-	3.0	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	5.7	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	17	44	ns
t _r	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_D = 15.7 \text{ A},$	- /	21	52	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 5 V, R_G = 4.7 Ω	-/	27	64	ns
t _f	Turn-Off Fall Time	(Note 4)	-	8	26	ns
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	//-	1.75	-	Ω

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	15.7	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	63	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 12 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, V_{DS} = 80 \text{ V}, I_{SD} = 15.7 \text{ A},$	-	38	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	50	-	nC

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 1 mH, I $_{AS}$ = 9.1 A, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. $I_{SD} \le 15.7$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

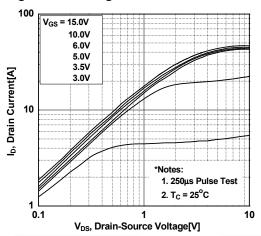


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

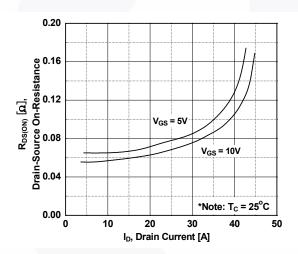


Figure 5. Capacitance Characteristics

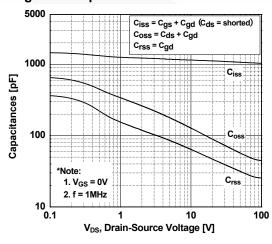


Figure 2. Transfer Characteristics

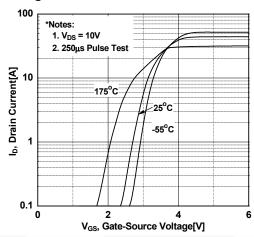


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

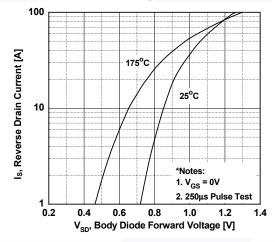
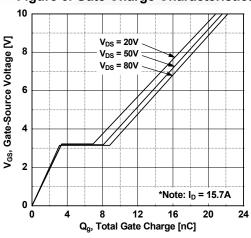


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

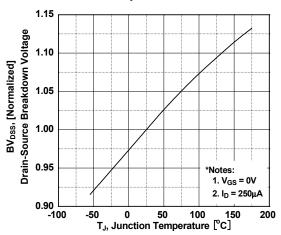


Figure 9. Maximum Safe Operating Area

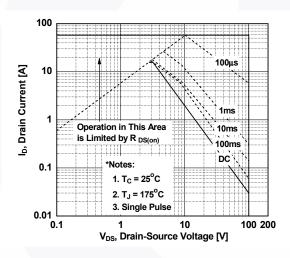


Figure 8. On-Resistance Variation vs. Temperature

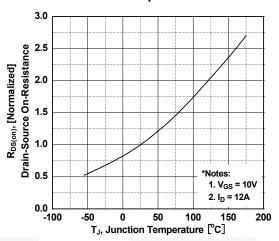


Figure 10. Maximum Drain Current vs. Case Temperature

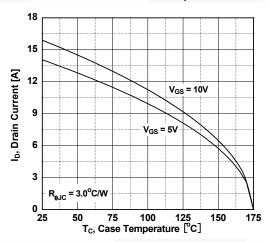
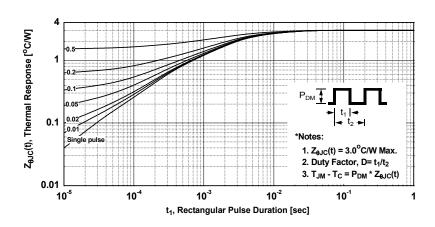


Figure 11. Transient Thermal Response Curve



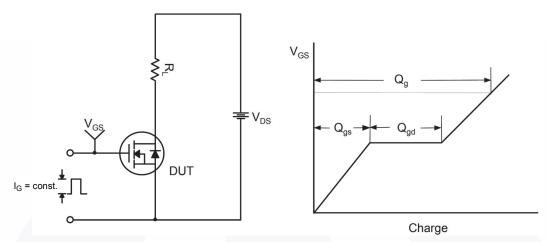


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms

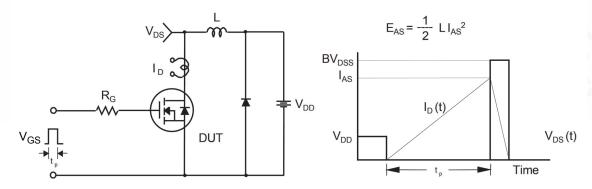


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

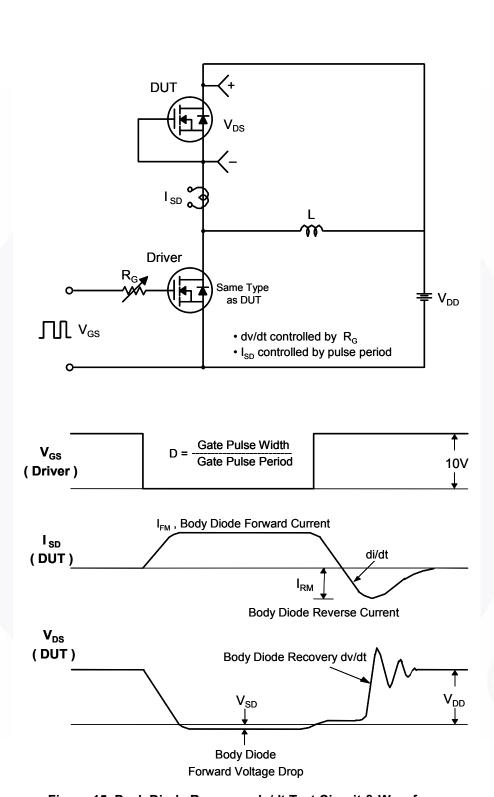


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

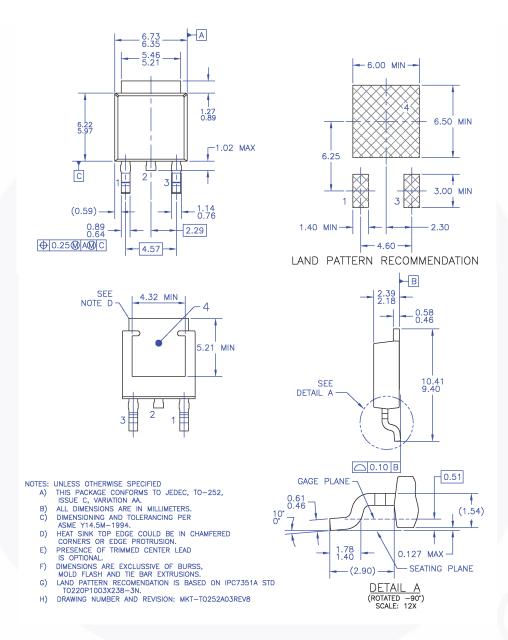


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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